

#### Is Now Part of



# ON Semiconductor®

# To learn more about ON Semiconductor, please visit our website at www.onsemi.com

Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (\_), the underscore (\_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (\_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at <a href="www.onsemi.com">www.onsemi.com</a>. Please email any questions regarding the system integration to Fairchild <a href="guestions@onsemi.com">guestions@onsemi.com</a>.

ON Semiconductor and the ON Semiconductor logo are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any EDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officer



### **BSS138**

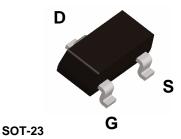
#### N-Channel Logic Level Enhancement Mode Field Effect Transistor

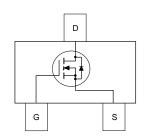
#### **General Description**

These N-Channel enhancement mode field effect transistors are produced using Fairchild's proprietary, high cell density, DMOS technology. These products have been designed to minimize on-state resistance while provide rugged, reliable, and fast switching performance. These products are particularly suited for low voltage, low current applications such as small servo motor control, power MOSFET gate drivers, and other switching applications.

#### **Features**

- 0.22 A, 50 V.  $R_{DS(ON)} = 3.5\Omega$  @  $V_{GS} = 10$  V  $R_{DS(ON)} = 6.0\Omega$  @  $V_{GS} = 4.5$  V
- High density cell design for extremely low R<sub>DS(ON)</sub>
- Rugged and Reliable
- Compact industry standard SOT-23 surface mount package





#### Absolute Maximum Ratings T<sub>A</sub>=25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V <sub>DSS</sub>	Drain-Source Voltage		50	V
V <sub>GSS</sub>	Gate-Source Voltage		±20	V
I <sub>D</sub>	Drain Current - Continuous	(Note 1)	0.22	А
	– Pulsed		0.88	
P <sub>D</sub>	Maximum Power Dissipation	(Note 1)	0.36	W
	Derate Above 25°C		2.8	mW/°C
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Temperature Range		-55 to +150	°C
TL	Maximum Lead Temperature for Soldering Purposes, 1/16" from Case for 10 Seconds		300	°C

#### **Thermal Characteristics**

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1)	350	°C/W
-----------------	---	----------	-----	------

**Package Marking and Ordering Information** 

Device Marking	Device	Reel Size	Tape width	Quantity	
SS	BSS138	7"	8mm	3000 units	

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Char	acteristics					
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, \qquad I_{D} = 250 \mu\text{A}$	50			V
<u>ΔBV<sub>DSS</sub></u> ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	$I_D$ = 250 $\mu$ A,Referenced to 25°C		72		mV/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	$V_{DS} = 50 \text{ V}, \qquad V_{GS} = 0 \text{ V}$			0.5	μΑ
		$V_{DS} = 50 \text{ V}, V_{GS} = 0 \text{ V T}_{J} = 125^{\circ}\text{C}$			5	μΑ
		$V_{DS} = 30 \text{ V}, \qquad V_{GS} = 0 \text{ V}$			100	nA
I <sub>GSS</sub>	Gate-Body Leakage.	$V_{GS} = \pm 20 \text{ V},  V_{DS} = 0 \text{ V}$			±100	nA
On Char	acteristics (Note 2)					
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}$ , $I_{D} = 1 \text{ mA}$	0.8	1.3	1.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	I <sub>D</sub> = 1 mA,Referenced to 25°C		-2		mV/°C
R <sub>DS(on)</sub>	Static Drain-Source	$V_{GS} = 10 \text{ V}, \qquad I_{D} = 0.22 \text{ A}$		0.7	3.5	Ω
	On–Resistance	$V_{GS} = 4.5 \text{ V}, \qquad I_D = 0.22 \text{ A}$		1.0	6.0	
I	On–State Drain Current	$V_{GS} = 10 \text{ V}, I_D = 0.22 \text{ A}, T_J = 125^{\circ}\text{C}$ $V_{GS} = 10 \text{ V}, V_{DS} = 5 \text{ V}$	0.2	1.1	5.8	A
I <sub>D(on)</sub>	Forward Transconductance	$V_{DS} = 10 \text{ V}, \qquad V_{DS} = 3 \text{ V}$ $V_{DS} = 10 \text{ V}, \qquad I_{D} = 0.22 \text{ A}$	0.2	0.5		S
g <sub>FS</sub>		V <sub>DS</sub> = 10V, I <sub>D</sub> = 0.22 A	0.12	0.5		3
Dynamic C <sub>iss</sub>	Characteristics Input Capacitance	V 25 V V 0 V		27		pF
Coss	Output Capacitance	$V_{DS} = 25 \text{ V}, \qquad V_{GS} = 0 \text{ V},$ $f = 1.0 \text{ MHz}$		13		pF
C <sub>rss</sub>	Reverse Transfer Capacitance	T = 1.0   Wil 12		6		pF
R <sub>G</sub>	Gate Resistance	V <sub>GS</sub> = 15 mV, f = 1.0 MHz		9		Ω
	g Characteristics (Note 2)	1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1				
t <sub>d(on)</sub>	Turn-On Delay Time	$V_{DD} = 30 \text{ V}, \qquad I_{D} = 0.29 \text{ A},$		2.5	5	ns
t <sub>r</sub>	Turn-On Rise Time	$V_{GS} = 10 \text{ V}, \qquad R_{GEN} = 6 \Omega$		9	18	ns
t <sub>d(off)</sub>	Turn-Off Delay Time			20	36	ns
t <sub>f</sub>	Turn–Off Fall Time			7	14	ns
$\overline{Q_g}$	Total Gate Charge	$V_{DS} = 25 \text{ V}, \qquad I_{D} = 0.22 \text{ A},$		1.7	2.4	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>GS</sub> = 10 V		0.1		nC
Q <sub>gd</sub>	Gate-Drain Charge			0.4		nC
Drain-So	ource Diode Characteristics	and Maximum Ratings		•	· U	
I <sub>s</sub>	Maximum Continuous Drain–Source				0.22	Α
V <sub>SD</sub>	Drain–Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, \qquad I_{S} = 0.44 \text{ A(Note 2)}$		0.8	1.4	V

#### Notes:

1.  $R_{\theta,JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins.  $R_{\theta,JC}$  is guaranteed by design while  $R_{\theta,CA}$  is determined by the user's board design.



a) 350°C/W when mounted on a minimum pad..

Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2.0%

#### **Typical Characteristics**

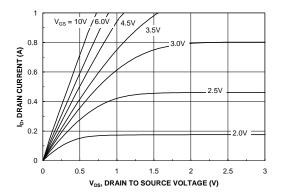


Figure 1. On-Region Characteristics.

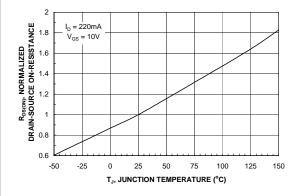


Figure 3. On-Resistance Variation with Temperature.

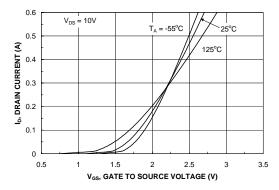


Figure 5. Transfer Characteristics.

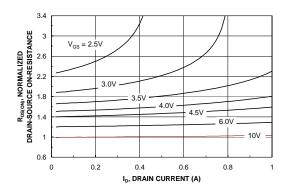


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

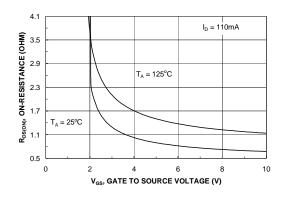


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

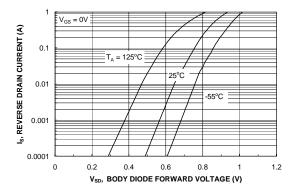
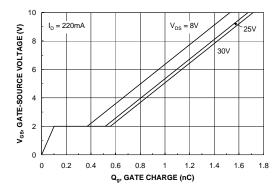


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

#### **Typical Characteristics**



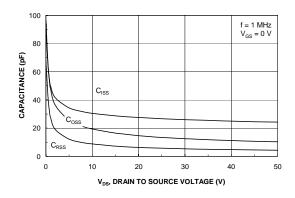


Figure 7. Gate Charge Characteristics.

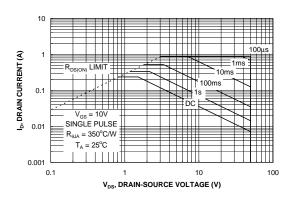


Figure 8. Capacitance Characteristics.

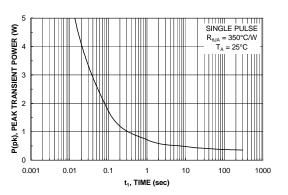


Figure 9. Maximum Safe Operating Area.



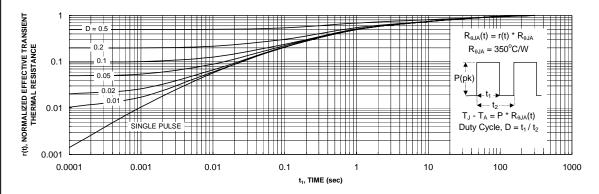


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1a. Transient thermal response will change depending on the circuit board design.



ON Semiconductor and in are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at <a href="www.onsemi.com/site/pdt/Patent-Marking.pdf">www.onsemi.com/site/pdt/Patent-Marking.pdf</a>. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and exp

#### **PUBLICATION ORDERING INFORMATION**

#### LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800–282–9855 Toll Free USA/Canada
Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81–3–5817–1050

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

# **Mouser Electronics**

**Authorized Distributor** 

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

**ON Semiconductor:** 

BSS138